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Attorney Docket No. P117-US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Schaadt, et al.

Art Unit: 1765

Serial No.: 10/666,998

Examiner: Not Yet Assigned

Filed: 9/17/03

For: **AN ETCHING METHOD IN FABRICATIONS OF MICROSTRUCTURES**

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-145

Sir:

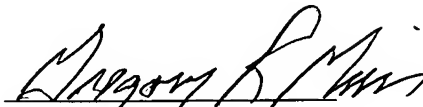
The attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO Form 1449. Copies of the cited references are enclosed.

No fee or certification is required in connection with this Information Disclosure Statement, since it is being submitted prior to the last of (1) issuance of a first official action on the merits and (2) expiration of the three month period following filing of the above-captioned application.

The above information is presented so that the Patent and Trademark Office can determine any materiality thereof to the claimed invention. It is respectfully requested that the information be considered during the prosecution of this application and that the cited documents be listed on the front page of any patent issuing from this application.

The Patent Office is authorized to charge our Deposit Account No. 501516 for any fee which it deems to be required to effect consideration of this statement.

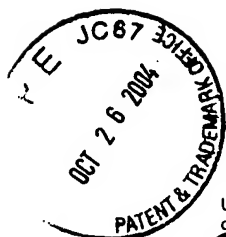
Respectfully submitted,

A handwritten signature in black ink, appearing to read "Gregory R. Muir", written over a horizontal line.

Gregory R. Muir
Attorney for Applicant(s)
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PTO/SB/08A (10-01)
Approved for use through 10/31/2002. OMB 0651-0031
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Substitute for form 1449A/PTO		Complete if Known			
		Application Number	10/666,998		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Filing Date	9/17/03		
		First Named Inventor	Schaadt		
		Art Unit	1765		
		Examiner Name	Not Yet Assigned		
Sheet	1	of	6	Attorney Docket Number	P117-US

U.S. PATENT DOCUMENTS					
Examiner Initials [*]	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,190,488	02-26-1980	Winters, H.F.	
		US- 4,310,380	12-12-1982	Flamm et al.	
		US- 4,498,953	02-12-1985	Cook et al.	
		US- 6,051,503	04-18-2000	Bhardwai, J.K.	
		US- 6,436,229	08-20-2002	Tai et al.	
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		US- 6,290,864 B1	09-18-2001	Patel et al.	
		US- 6,355,181 B1	03-12-2002	McQuarrie, A.D.	
		US- 2001/0002663 A1	06-07-2001	Tai et al.	
		US- 5,439,553	08-08-1995	Grant et al.	
		US- 2002/0033229 A1	03-21-2002	Leboulitz et al.	
		US- 2002/0196524 A1	12-26-2002	Huibers, et al.	
		US- 2003/0054588 A1	03-20-2003	Patel, et al.	
		US- 5,726,480	03-10-1998	Pister, K.S.	
		US- 2002/0185699	12-12-2002	Reid	
		US- 2002/0121502 A1	09-15-2002	Patel, et al.	
		US- 5,835,256	11-10-1998	Huibers, A.	
		US- 2002/0047172 A1	04-25-2002	Reid	
		US- 2003/0166342 A1	09/04/03	Chinn, et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials [*]	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
		EP-0704884-A2	04-03-1996	Mehta, J.		
		EP-0822582-A2	02-04-1998	Bhardwai, J.K.		
		EP-0822584-A2	04-04-1998	Bhardwai, J.K.		
		WO-99/49506	09-30-1999	McQuarrie, A.D.		
		EP-0878824-A2	11-18-1998	McQuarrie et al.		
		EP-0878824-A3	01-19-2000	McQuarrie et al.		
		JP-1982/57098679-A	06-18-1982	Tsunetoshi, A.		
		JP-1983/58130529-A	08-04-1983	Yoshihiro et al.		
		JP-1985/60057938-A	04-03-1985	Katsumi et al.		
		WO-98/32163	07-23-1998	Tai et al.		

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Sheet	2	of	6	Attorney Docket Number	P117-US

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		Number - Kind Code ² (if known)			
		US- 6,409,876 B1	06-25-2002	McQuarrie, et al.	
		US- 6,396,619 B1	05-28-2002	Huibers, et al.	
		US- 6,576,489 B2	06/10/03	Leung, et al.	
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		US- 6,197,610 B1	03/06/2001	Toda	
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		US- 6,290,864	04/18/01	Patel, et al.	
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		US- 2004/0035821	2/26/04	Doan, et al.	
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		JP-1997/09251981-A	09-22-1997	Kazuaki et al.		
		JP-1998/10313128-A	11-24-1998	Hanmin et al.		
		JP-1998/10317169-A	12-02-1998	McQuarrie et al.		
		JP-1986/61187238-A	08-20-1986	Nobuo et al.		
		JP-1986/61270830-A	12-01-1986	Toru, T.		
		JP-1987/62071217-A	04-01-1987	Toru et al.		
		JP-1988/63155713-A	06-28-1988	Tadashi, F.		
		JP-1986/61053732-A	03-17-1986	Arata et al.		
		JP-1986/61134019-A	06-21-1986	Shinii et al.		
		JP-1986/61181131-A	08-13-1986	Shinii et al.		

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				Filing Date	9/17/03
				First Named Inventor	Schaadt
				Art Unit	1765
				Examiner Name	Not Yet Assigned
Sheet	3	of	6	Attorney Docket Number	P117-US

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		US-			
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		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
		JP-1989/01208834-A	08-22-1989	Nobuo et al.		
		JP-1989/10217921-A	08-31-1989	Tsuneo et al.		
		JP-1990/02250323-A	10-08-1990	Susumu et al.		
		JP-1991/03012921-A	01-21-1991	Nobuo et al.		
		JP-1992/04096222-A	03-27-1992	Atsuyuki, A.		
		JP-1995/07029823-A	01-31-1995	Hiroshi, T.		

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		Filing Date	9/17/03
		First Named Inventor	Schaadt
		Group Art Unit	1765
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	P117-US
Sheet	4	of	6

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials²	Cite No.¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T²
		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F ₂ and XeF ₂ Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
		GLIDEMEISTER, J.M., "Xenon Difluoride Etching System" (Nov. 17, 1997).	
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		HECHT et al., "A Novel X-ray Photoelectron Spectroscopy Study of the Al/SiO ₂ Interface", J. Appl. Phys. Vol. 57 (June 15, 1985), pp. 5256-5261.	
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		FLAMM et al., "XeF ₂ and F-Atom Reactions with Si: Their Significance for Plasma Etching", Solid State Technol. 26, 117 (1983).	
		IBBOTSON et al., "Plasmaless Dry Etching of Silicon with Fluorine-containing Compounds", J. Appl. Phys. Vol. 56 No. 10 (Nov. 1984), pp. 2939-2942.	
		IBBOTSON et al., "Comparison of XeF ₂ and F-atom Reactions with Si and SiO ₂ ", Applied Physics Letter, Vol. 44, 1129 (1984).	
		STRELLER et al., "Selectivity in Dry Etching of Si (100) and XeF ₂ and VUV Light", Elsevier Science B.V., Applied Surface Science Vol. 106 (1996), pp. 341-346.	
		VUGTS et al., "Si/XeF ₂ Etching: Temperature Dependence", J. Vac. Sci. Technol. A 14(5) (Sep/Oct 1996), pp. 2766-2774.	
		WINTERS, H.F., "Etch Products from the Reaction of XeF ₂ with SiO ₂ , SiO ₃ , Si ₃ N ₄ , SiC, and Si in the Presence of Ion Bombardment", J. Vac. Sci. Technol. B 1(4) (Oct/Dec 1983), pp. 927-931.	

Examiner Signature		Date Considered	
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	Application Number	10/666,998			
	Filing Date	9/17/03			
	First Named Inventor	Schaadt			
	Group Art Unit	1765			
	Examiner Name	Not Yet Assigned			
	Attorney Docket Number	P117-US			
Sheet	5	of	6		

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
		WINTERS et al., "The Etching of Silicon with XeF ₂ Vapor", Appl. Phys. Letter, Vol. 34(1) (January 1, 1979), pp. 70-73.	
		XACTIX, Inc., Marketing Brochure (June 27, 1999).	
		"Xenon Difluoride Isotropic Etch System: Seeing is Believing", Surface Technology Systems Ltd. brochure, Newport, UK (date unknown).	
		CHU et al., "Controlled Pulse-Etching with Xenon Difluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 665-668 (abstract only).	
		BASSOM et al., "Modeling and Optimizing XeF ₂ -enhanced FIB Milling of Silicon", 25th International Symposium for Testing and Failure Analysis, Santa Clara, CA (Nov. 14 -18, 1999), pp. 255-261 (abstract only).	
		KOHLER et al., "Fabrication of Microlenses by Plasmaless Isotropic Etching Combined with Plastic Moulding", Sens. Actuators A, Phys. (Switzerland), Vol. A53, No. 1-3 (May 1996), pp. 361-363 (abstract only).	
		CHAN et al., "Gas Phase Pulse Etching of Silicon for MEMS with Xenon Difluoride", Engineering Solutions for the Next Millenium: 1999 IEEE Canadian Conference on Electrical and Computer Engineering, Edmonton, Alberta, Vol. 3 (May 9 - 12, 1999), pp. 1637-1642 (abstract only).	
		CHANG et al., "Gas-Phase Silicon Micromachining with Silicon Difluoride", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).	

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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
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		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/XeF ₂ Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
		SEBEL et al., "Silicon Etch Rate Enhancement by Traces of Metal", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 17, No. 3, (May/June 1999), pp. 755-762 (abstract only).	
		SUGANO et al., "Study on XeF ₂ Pulse Etching Using Wagon Wheel Pattern", Proceedings of the 1999 International Symposium on Micromechanics and Human Science: Towards the New Century, Nagoya, Japan (Nov. 23 - 26, 1999), pp. 163-167 (abstract only).	
		WANG et al., "Gas-Phase Silicon Etching with Bromine Trifluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 2 (June 16 - 19, 1997), pp. 1505-1508 (abstract only).	
		MUTHUKUMARAN et al., "Gas-Phase Xenon Difluoride Etching of Microsystems Fabricated Through the Mitel 1.5- μ m CMOS Process", Can. J. Electr. Comput. Eng. (Canada), Vol. 25, No. 1 (Jan. 2000), pp. 35-41 (abstract only).	
		TODA et al., "Thin Beam Bulk Micromachining Based on RIE and Xenon Difluoride Silicon Etching", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 671-674.	
		SEBEL et al., "Etching of Si Through a Thick Condensed XeF ₂ Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 5 (Sep/Oct 2000), pp. 2090-2097 (abstract only).	

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